SG2M025075TJ-A

TriQSiC™ 750V Silicon Carbide Power MOSFET G2

Features

-
-
-
-
-
-
-

Benefits

-
-
-
-
-



Applications

-
-
-
-

Table 1 Key perform e

Table of contents

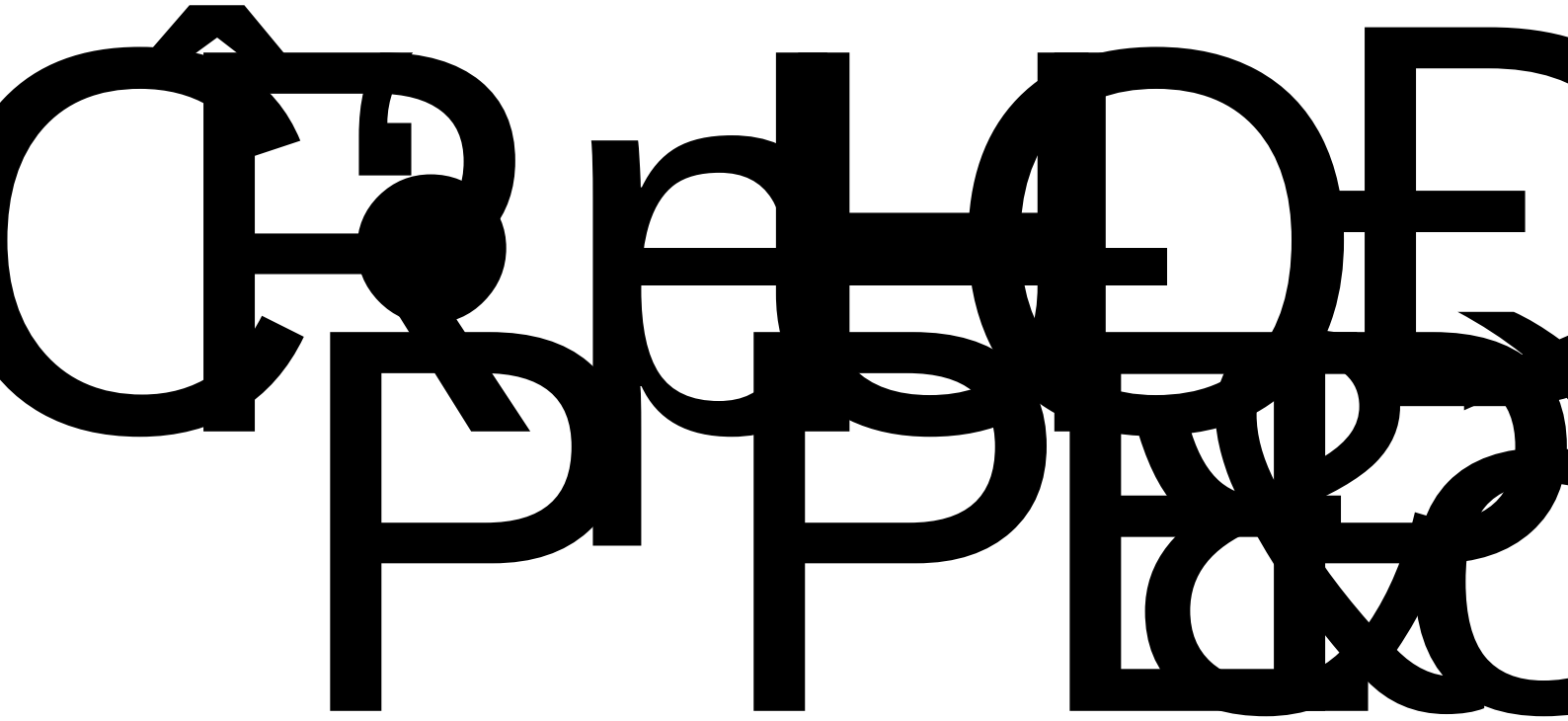
Features **1**

Benefits ..... .- ! -

1 Maximum ratings

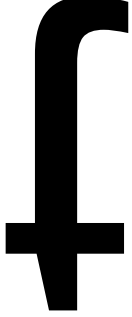
Table 2 Maximum rating

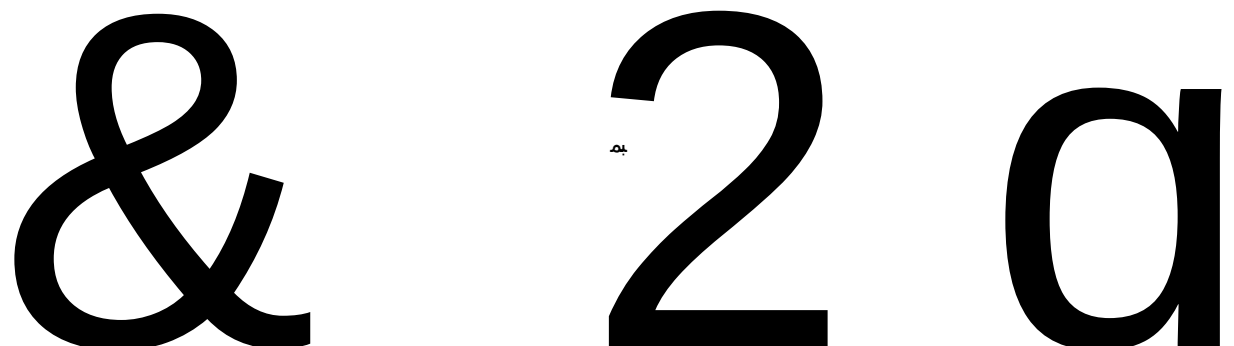
Symbol	Parameter	Value	Unit	Test Conditions	Note
				≤	





SG2M025075TJ-A





3.3 Switching characteristics

Table 6 Dynamic characteristics

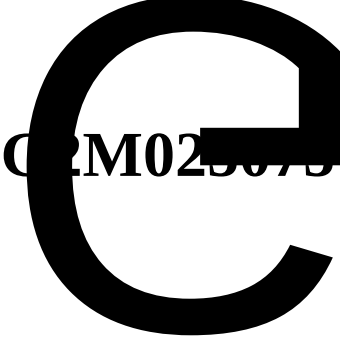
Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note

Table 7 Body diode characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note

SG2M025075TJ-A

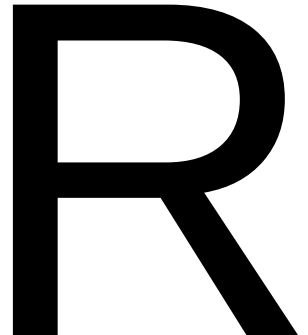
755ig ^ o r d



SC2M0250J5TJ-A

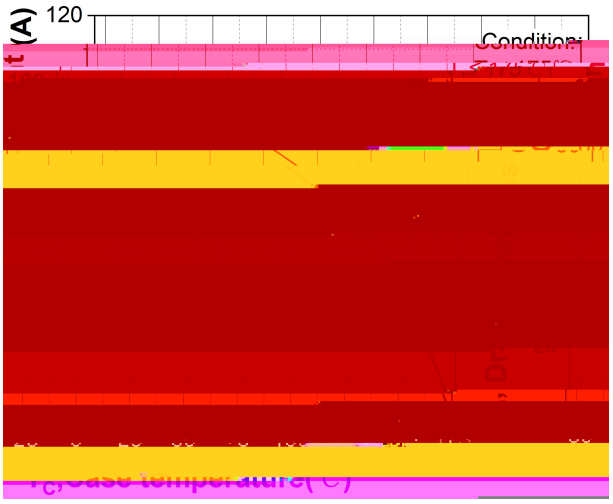


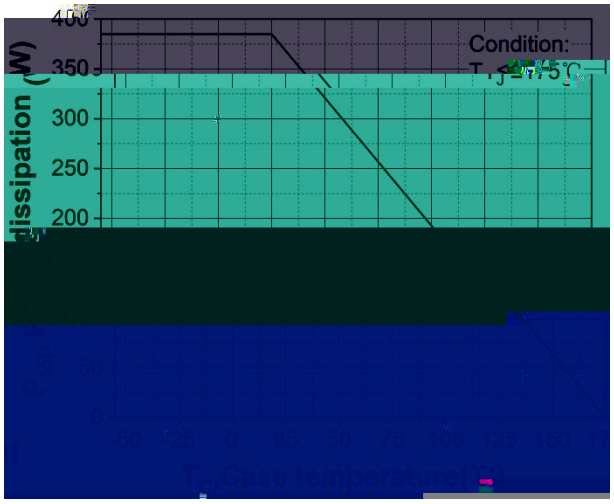
B €8 。µ∀€(∩,··· ⅄„— • •

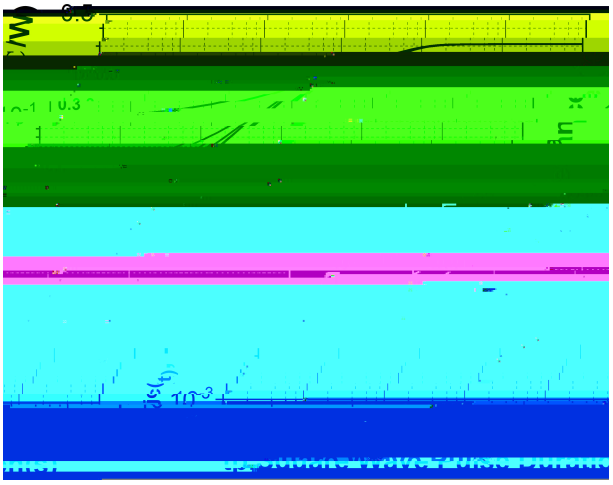


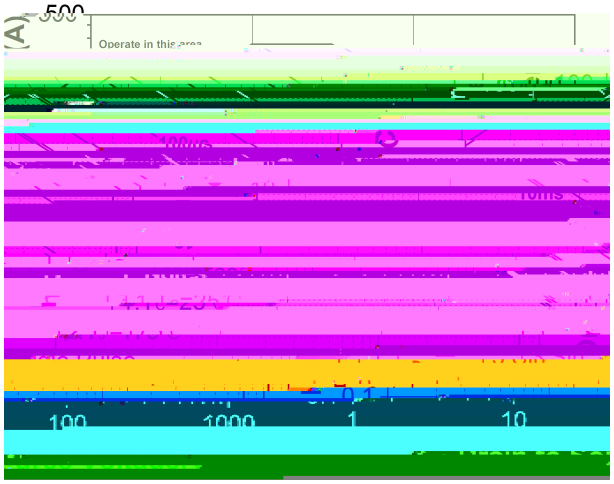
SG2M025075TJ-A

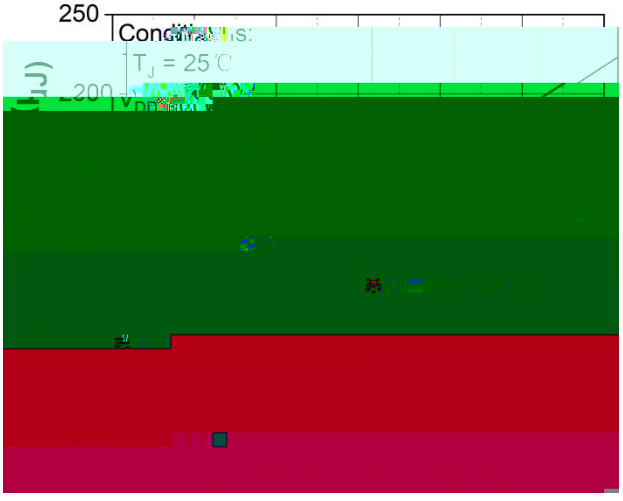
SG2M025075TJ-A

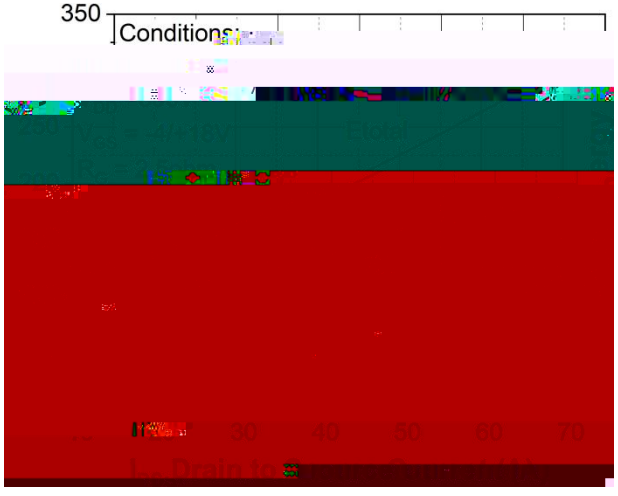






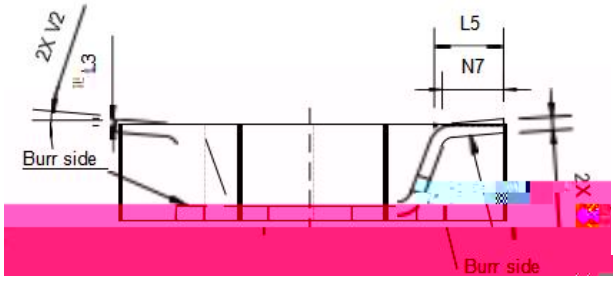


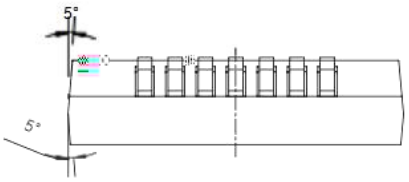




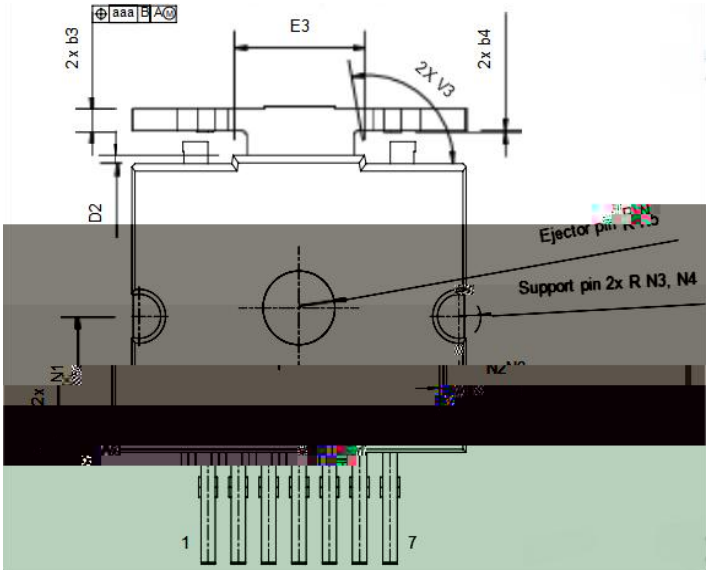
SG2M025075TJ-A

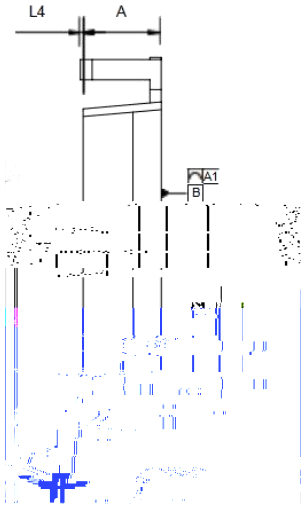
5 Package drawing

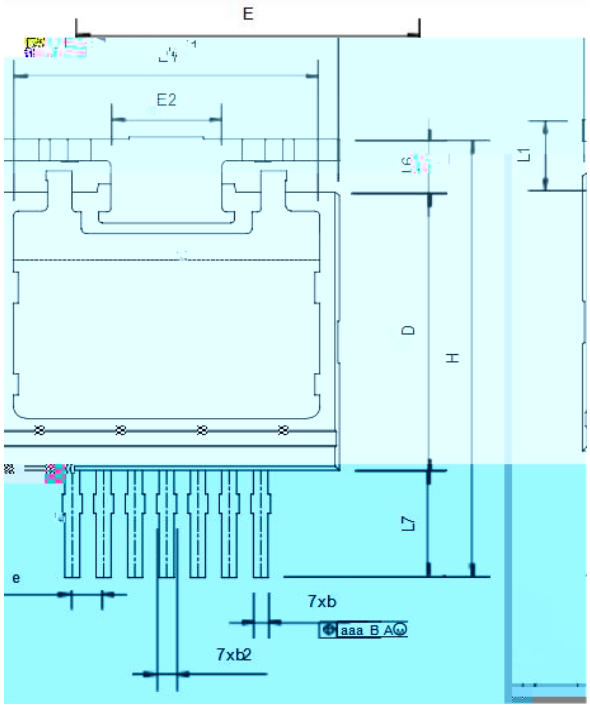


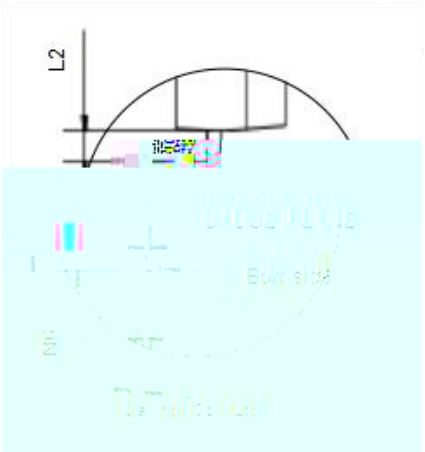


SYMBO	Common DIMENSIONS MILLIMETER		
	MIN.	NOM.	MAX.
A	3.40	3.50	3.60
A1		0.05	
b	0.60	0.7	
E	14.10	14.30	14.4
E1	12.50	12.80	12.9
E2	4.66	4.85	5.0
E3	5.66	5.85	6.0
e		1.27	
H	18.00	18.30	18.6
L	2.42	2.62	2.8
L1	2.62	2.82	3.0
L2	0.90	1.00	1.1
L3	1.10	1.20	1.3
L4	0.075	0.125	0.17
L5	2.38	2.48	2.5
L6	2.14	2.24	2.3
L7	4.44	4.54	4.6
N1	5.40	5.50	5.6

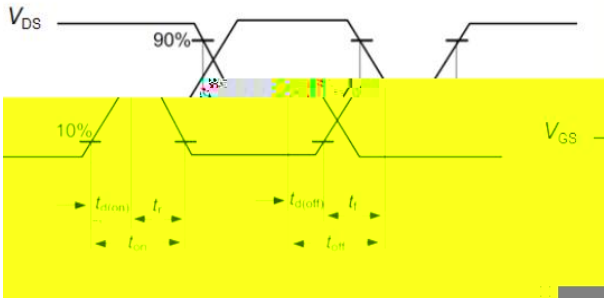


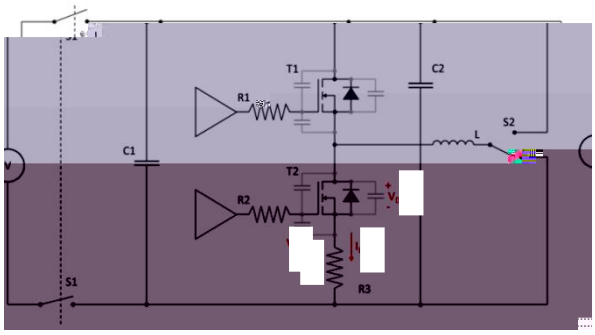


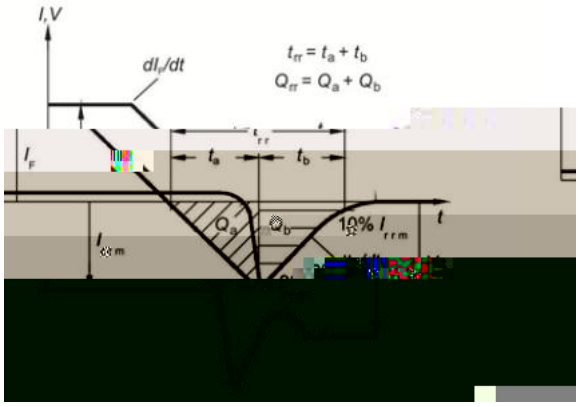




6 Test conditions







SG2M025075TJ-A

750V SiC Power MOSFET



SG2M025075TJ-A